

Super Barrier Rectifier ™

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

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Characteristics	Values	Units		
I _{F(AV)} Rectangular Waveform	60	Α		
V_{RRM}	150	V		
V _F @30A, Tj=125 ^o C	0.73	V, typ		
Tj (operating/storage)	-65 to 175	°C		

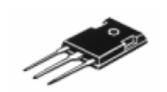
ELECTRICAL:

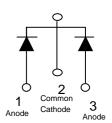
- * Low Forward Voltage Drop
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, fast switching capability
- * 175°C Operating Junction Temperature

Device optimized for low forward voltage drop to maximize efficiency in Power Supply applications

MECHANICAL:

* Molded Plastic TO-3P package





Maximum Ratings and Electrical Characteristics (at 25°C unless otherwise specified)

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	SYMBOL			UNITS			
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	$egin{array}{c} egin{array}{c} egin{array}{c} V_{RM} \ V_{RRM} \end{array}$	150		Volts			
Average Rectified Forward Current (Rated V _R -20Khz Square Wave) - 50% duty cycle	Io	60		Amps			
Peak Forward Surge Current - 1/2 60hz	I _{FSM}	350		Amps			
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I _{RRM}	3		Amps			
Instantaneous Forward Voltage (per leg) $I_F = 30A$; $T_J = 25^{\circ}C$ $I_F = 30A$; $T_J = 125^{\circ}C$	V _F	Тур 	Max 0.93 0.77	Volts			
Maximum Instantaneous Reverse Current at Rated V_{RM} $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I _R *	Typ 	Max 100 10	uA mA			
Maximum Rate of Voltage Change (at Rated V_R)	dv/dt	10,000		V/uS			
Maximum Thermal Resistance JC (per leg)	$R\theta_{JC}$	2		°C/W			
Operating and Storage Junction Temperature	T」	-65 to +175		°C			

 $^{^{\}star}$ Pulse width < 300 uS, Duty cycle < 2%

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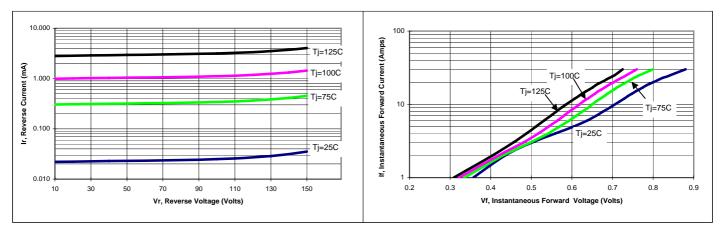


Figure 1: Typical Reverse Current (per leg)

Figure 2: Typical Forward Voltage (per leg)

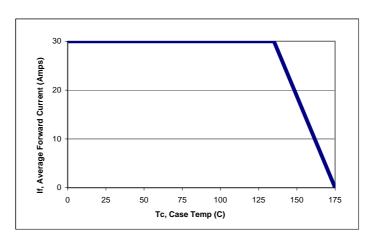


Figure 3: Current Derating, Case (per leg)

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